

PF0414A

MOS FET Power Amplifier Module for DCS 1800 Handy Phone

HITACHI

ADE-208-431B (Z)
3rd Edition
December 1997

Application

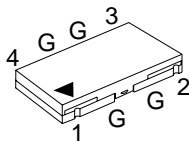
For DCS 1800 class1 1710 to 1785 MHz.

Features

- 3stage amplifier
- Small package: 0.2cc
- High efficiency: 45% Typ
- High speed switching: 0.9 μ sec

Pin Arrangement

• RF-K



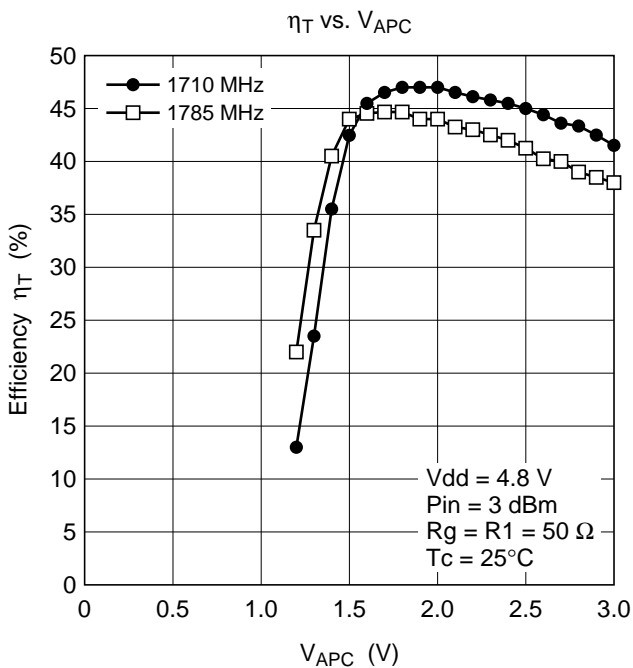
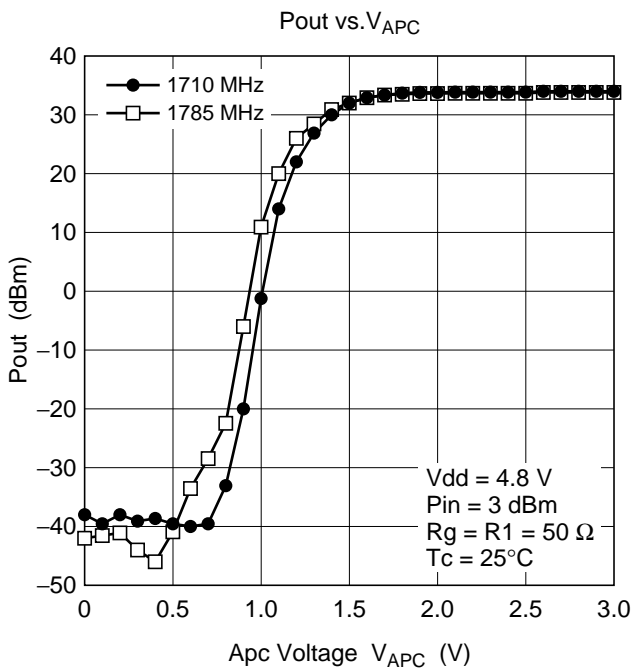
1: Pin
2: Vapc
3: Vdd
4: Pout
G: GND

Absolute Maximum Ratings (T_c = 25°C)

Item	Symbol	Rating	Unit
Supply voltage	V _{DD}	11	V
Supply current	I _{DD}	3	A
V _{APC} voltage	V _{APC}	6	V
Input power	P _{in}	20	mW
Operating case temperature	T _c (op)	-30 to +100	°C
Storage temperature	T _{stg}	-30 to +100	°C
Output power	P _{out}	3	W

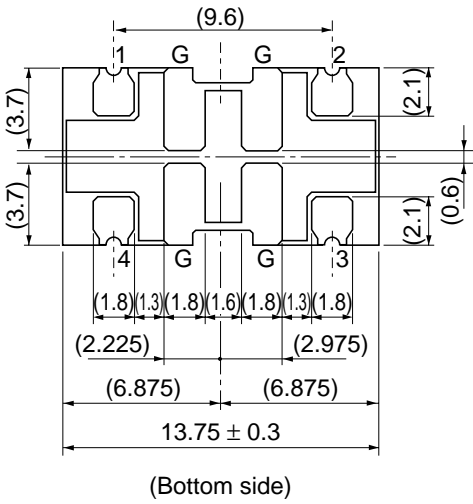
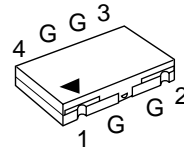
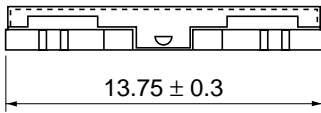
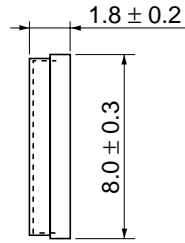
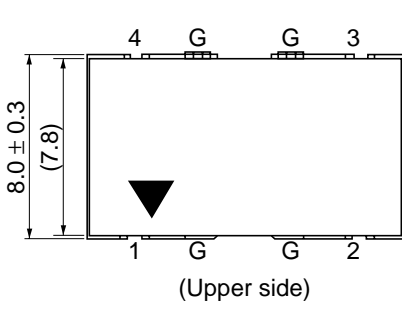
Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	1710	—	1785	MHz	
Control voltage range	V_{APC}	0.5	—	3	V	
Drain cutoff current	I_{DS}	—	—	100	μA	$V_{DD} = 11\text{ V}, V_{APC} = 0\text{ V}$
Total efficiency	η_T	37	45	—	%	$P_{in} = 2\text{ mW}, V_{DD} = 4.8\text{ V},$ $P_{out} = 1.8\text{ W (at APC controlled)},$
2nd harmonic distortion	2nd H.D.	—	-45	-35	dBc	$R_L = R_g = 50\ \Omega, T_c = 25^\circ\text{C}$
3rd harmonic distortion	3rd H.D.	—	-45	-35	dBc	
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	$P_{out} (1)$	2.0	2.4	—	W	$P_{in} = 2\text{ mW}, V_{DD} = 4.8\text{ V},$ $V_{APC} = 3\text{ V}, R_L = R_g = 50\ \Omega,$ $T_c = 25^\circ\text{C}$
Output power (2)	$P_{out} (2)$	1.2	1.5	—	W	$P_{in} = 2\text{ mW}, V_{DD} = 4.3\text{ V},$ $V_{APC} = 3\text{ V}, R_L = R_g = 50\ \Omega,$ $T_c = 80^\circ\text{C}$
Isolation	—	—	-40	-30	dBm	$P_{in} = 2\text{ mW}, V_{DD} = 4.8\text{ V},$ $V_{APC} = 0.5\text{ V}, R_L = R_g = 50\ \Omega,$ $T_c = 25^\circ\text{C}$
Switching time	t_r, t_f	—	0.9	2	μs	$P_{in} = 2\text{ mW}, V_{DD} = 4.8\text{ V},$ $P_{out} = 1.8\text{ W}, R_L = R_g = 50\ \Omega,$ $T_c = 25^\circ\text{C}$
Stability	—	No parasitic oscillation			—	$P_{in} = 2\text{ mW}, V_{DD} = 6\text{ V},$ $I_{ds} \leq 0.9\text{ A (only pulsed)},$ $P_{out} \leq 1.8\text{ W (at APC controlled)},$ $R_g = 50\ \Omega, t = 20\text{ sec.}, T_c = 25^\circ\text{C},$ Output VSWR = 10 : 1 All phases



Package Dimensions

Unit: mm



Remark:
Coplanarity of bottom side of terminals are less than 0 ± 0.1 mm.

Hitachi Code	RF-K
JEDEC	—
EIAJ	—
Weight (reference value)	—

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